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FDD3670

100V N-Channel PowerTrench[®] MOSFET

General Description

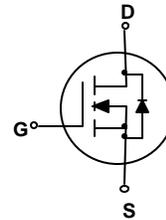
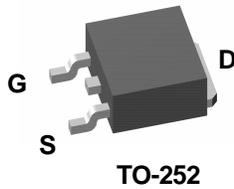
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(ON)}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

Features

- 34 A, 100 V. $R_{DS(ON)} = 32\text{ m}\Omega @ V_{GS} = 10\text{ V}$
 $R_{DS(ON)} = 35\text{ m}\Omega @ V_{GS} = 6\text{ V}$
- Low gate charge (57 nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1)	34	A
	Drain Current – Pulsed (Note 3)	100	
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ (Note 1)	83	W
	@ $T_A = 25^\circ\text{C}$ (Note 1a)	3.8	
	@ $T_A = 25^\circ\text{C}$ (Note 1b)	1.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	1.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDD3670	FDD3670	13"	16mm	2500 units

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 50\text{ V}, I_b = 7.3\text{ A}$			360	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				7.3	A

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_b = 250\ \mu\text{A}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_b = 250\ \mu\text{A}$, Referenced to 25°C		92		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			10	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics

 (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_b = 250\ \mu\text{A}$	2	2.5	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_b = 250\ \mu\text{A}$, Referenced to 25°C		-7.2		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_b = 7.3\text{ A}$ $V_{GS} = 10\text{ V}, I_b = 7.3\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 6\text{ V}, I_b = 7.0\text{ A}$		22 39 24	32 56 35	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	25			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_b = 7.3\text{ A}$	15	31		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V},$		2490		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		265		pF
C_{rss}	Reverse Transfer Capacitance			80		pF

Switching Characteristics

 (Note 2)

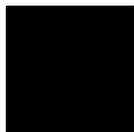
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}, I_b = 1\text{ A},$		16	26	ns
t_r	Turn-On Rise Time	$V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		10	18	ns
$t_{d(off)}$	Turn-Off Delay Time			56	84	ns
t_f	Turn-Off Fall Time			25	40	ns
Q_g	Total Gate Charge	$V_{DS} = 50\text{ V}, I_b = 7.3\text{ A},$		57	80	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 10\text{ V}$		11		nC
Q_{gd}	Gate-Drain Charge			15		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current				2.7	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.7\text{ A}$ (Note 2)		0.72	1.2	V

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2oz copper.



b) $R_{\theta JA} = 96^\circ\text{C/W}$ on a minimum mounting pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%
- Pulse I_d refers to Figure.9 Forward Bias Safe Operation Area.

Typical Characteristics

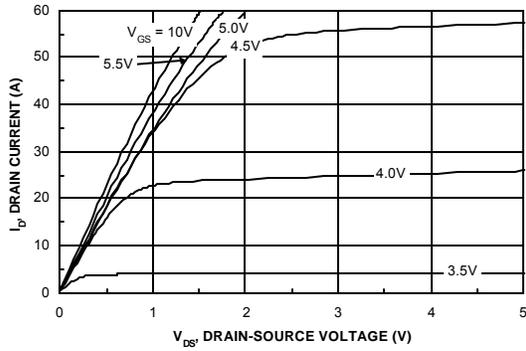


Figure 1. On-Region Characteristics.

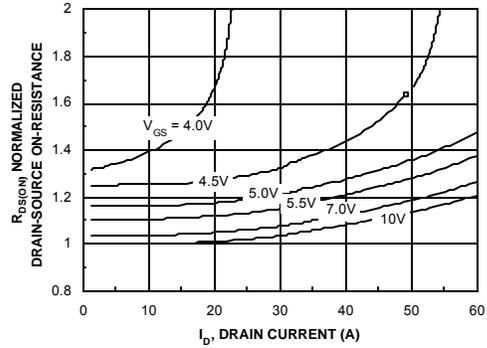


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

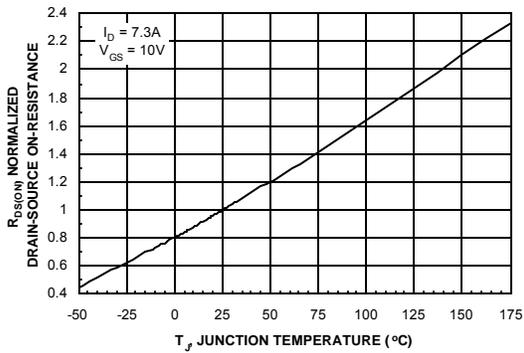


Figure 3. On-Resistance Variation with Temperature.

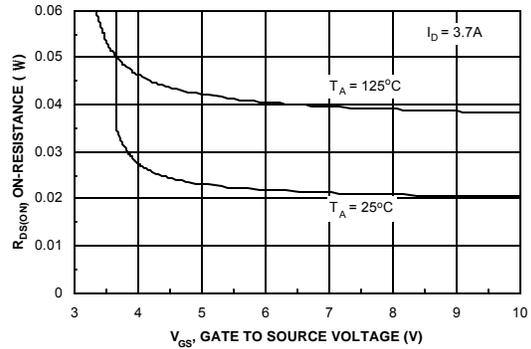


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

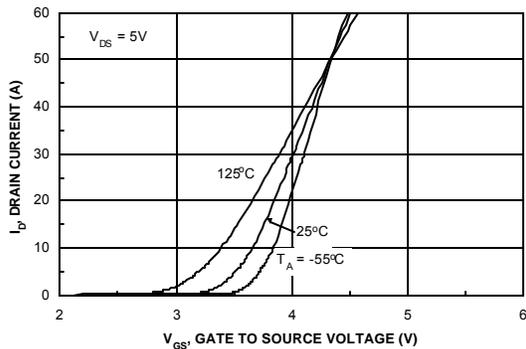


Figure 5. Transfer Characteristics.

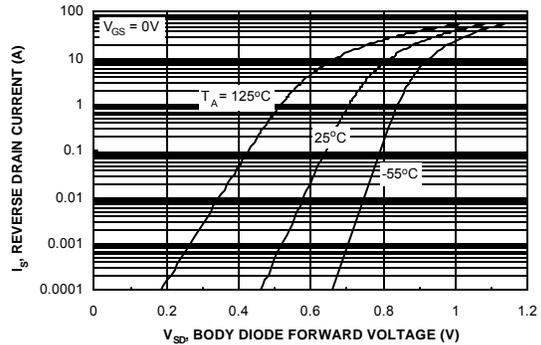


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

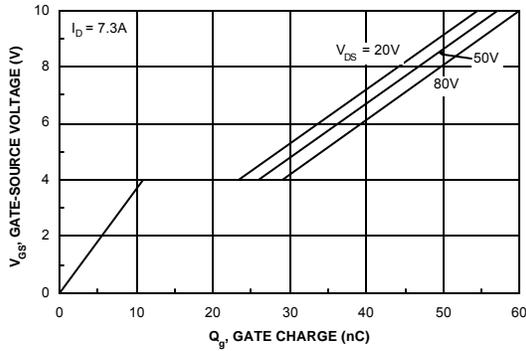


Figure 7. Gate Charge Characteristics.

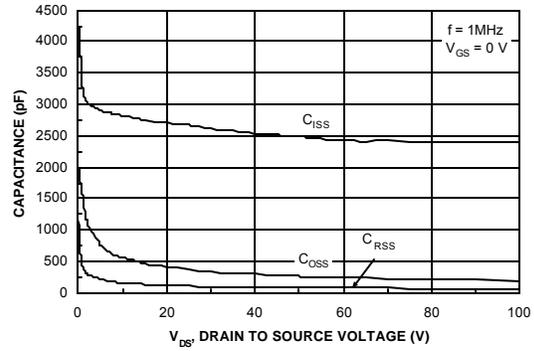


Figure 8. Capacitance Characteristics.

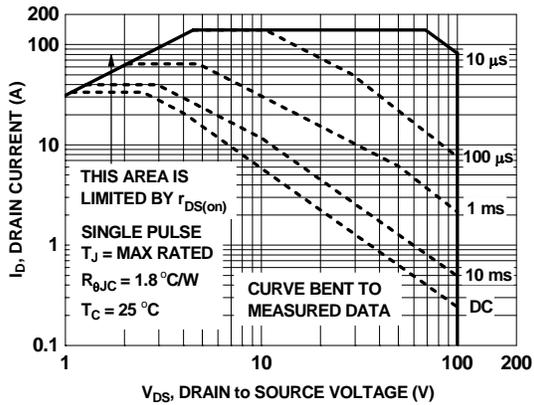


Figure 9. Forward Bias Safe Operating Area.

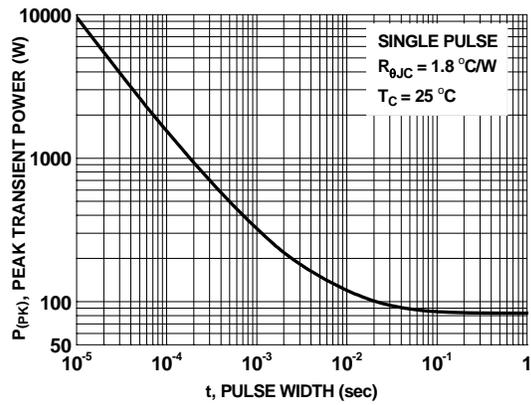


Figure 10. Single Pulse Maximum Power Dissipation.

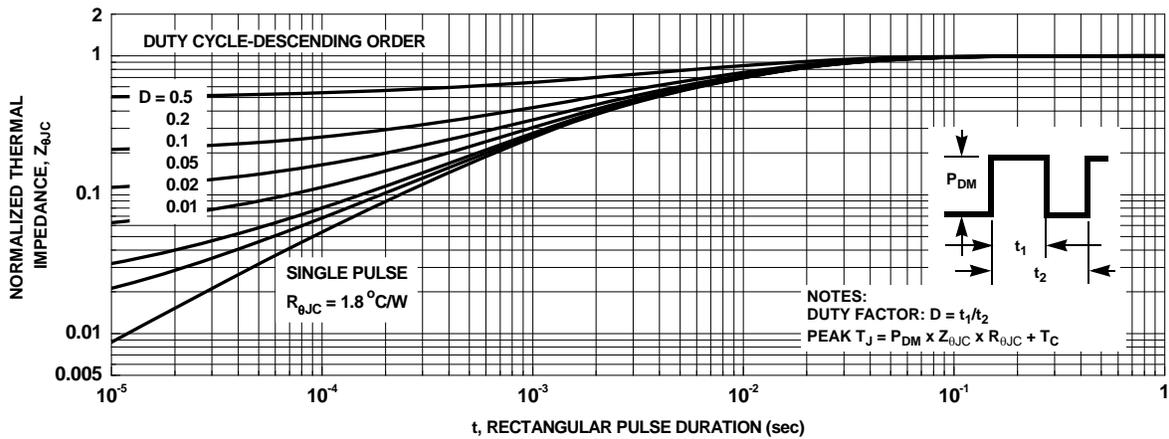


Figure 11. Junction-to-Case Transient Thermal Response Curve

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